



US005569610A

United States Patent [19]**Zhang et al.**[11] **Patent Number:** **5,569,610**[45] **Date of Patent:** **Oct. 29, 1996**

[54] **METHOD OF MANUFACTURING MULTIPLE POLYSILICON TFTS WITH VARYING DEGREES OF CRYSTALLINITY**

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[21] Appl. No.: **207,185**

[22] Filed: **Mar. 8, 1994**

[30] **Foreign Application Priority Data**

Mar. 12, 1993 [JP] Japan 5-079004
Mar. 12, 1993 [JP] Japan 5-079005

[51] Int. Cl.⁶ **H01L 21/84**

[52] U.S. Cl. **437/21; 437/41; 437/101; 437/174**

[58] Field of Search 437/173, 21, 41 TFT, 437/101, 174

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[57] **ABSTRACT**

Method of fabricating a semiconductor circuit is initiated with formation of an amorphous silicon film. Then, a second layer containing at least one catalytic element is so formed as to be in intimate contact with the amorphous silicon film, or the catalytic element is introduced into the amorphous silicon film. This amorphous silicon film is selectively irradiated with laser light or other equivalent intense light to crystallize the amorphous silicon film.

13 Claims, 5 Drawing Sheets